

Reliability Report: DS1808

Process: 1P, 1M, 5.0um, 30V NF & PF, UVNd, UVPd, N+ESD, TEOS Spacer,

Passivation w/Nov TEOS Oxide-Nitride

Metal: Al / 0.5% Cu / 0.8% Si

Gate Ox Thickness: 225 Å

Pin Count: 16

Summary Data with Chi-Square Distribution Assumed.
Stress Ambient Temperature and Voltage to
Field Ambient Temperature And Voltage

Cf: 60%

Tuse: 25 °C

Assembly: ATP (Amkor, PI)

Ea: 0.7

Vuse: 5.5 Volts

Package: SOIC

β: 0

Body Size: 150x1.4

DESCRIPTION	VEHICLE	REV	DATE CODE	CONDITION	READPOINT	QUANTITY	FAILS	FILE #	DEVICE HRS
HIGH TEMPERATURE OPERATING LIFE									
HIGH VOLTAGE LIFE	DS1808	A2	0133	125C, 6.0 V (PSA) & +13.2 V (PS	6	HOURS	80	0	452720
	DS1808	A2	0133	125C, 6.0 V (PSA) & +13.2 V (PS	336	HOURS	80	0	24899612
DEVICE HRS: 2.54E+07						TOTALS:	0		
FAILURE RATE					MTBF (yrs): 3158	FITS:	36		

PRODUCT	REV	DIE SIZE (x)	DIE SIZE (y)	No. of Transistors
DS1808	A2	159	80	1700